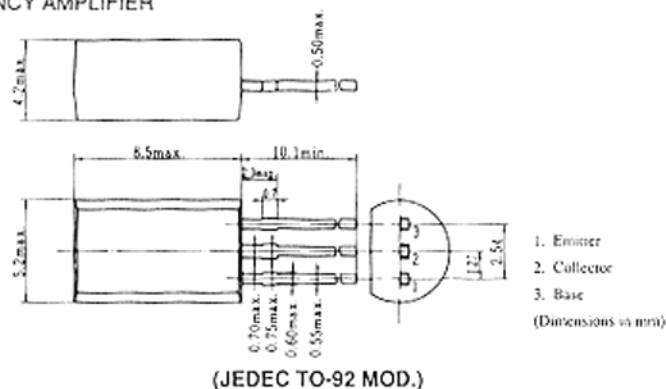


2SC4367

SILICON NPN EPITAXIAL
HIGH FREQUENCY AMPLIFIER

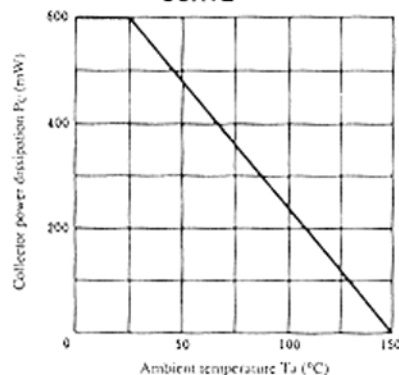


1. Emitter
2. Collector
3. Base
(Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC4367	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	100	mA
Collector peak current	$i_{C(peak)}$	200	mA
Collector power dissipation	P_C	600	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

■ MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	30	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 3mA, R_{BE} = \infty$	20	—	—	V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	3	—	—	V
Collector cutoff current	I_{CBO}	$V_{CB} = 10V, I_E = 0$	—	—	1.0	μA
DC current transfer ratio	h_{FE}	$V_{CE} = 10V, I_C = 10mA$	40	—	—	—
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 4mA$	—	—	1.0	V
Gain bandwidth product	f_T	$V_{CE} = 10V, I_C = 10mA$	600	1000	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	1.0	—	pF

TYPICAL OUTPUT CHARACTERISTICS

